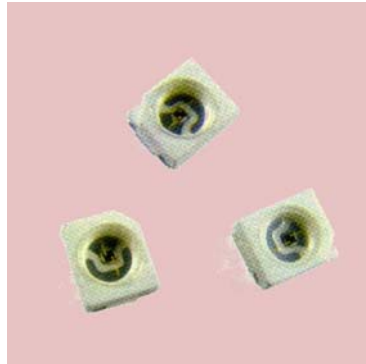


Ultraviolet selective GaN based UV sensor

AG38S-SMD



Features

- Broadband UVA-UVB-UVC selective photodiode
- Optimally suited for low-cost UV consumer applications
- Intrinsicy insensitive in the visible due to the wide-bandgap semiconductor material GaN
- SMD package with quartz window
- 0,076 mm² active chip area
- High speed and low noise

Eigenschaften

- Breitbandige UVA-UVB-UVC selektive Photodiode
- Optimale Eignung für kostengünstige UVA-Messung
- Inhärent unempfindlich gegen sichtbares Licht durch GaN-Halbleiter mit hoher Bandlücke
- SMD Gehäuse mit Quarzfenster
- 0,076 mm² aktive Chipfläche
- Schnelle Photodiode mit niedrigem Rauschen

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Maximum Ratings

Parameter	Symbol	Value	Unit
Operating temperature range	T_{opt}	-25 ... +80	°C
Reverse voltage	V_{Rmax}	5	V

General Characteristics

($T_a = 25\text{ °C}$)

Parameter	Symbol	Value	Unit
Active area	A	0.076	mm ²
Dark current at 0.1 V reverse bias	I_d	100	fA
Capacitance	C	24	pF
Short circuit current at bright sun	I_0	ca. 200	nA

Spectral Characteristics

($T_a = 25\text{ °C}$)

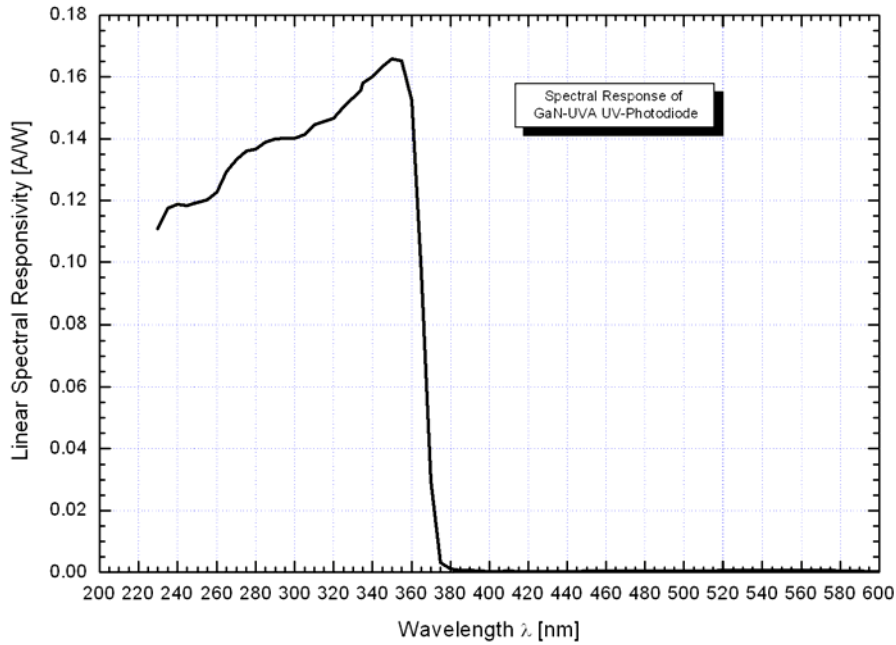
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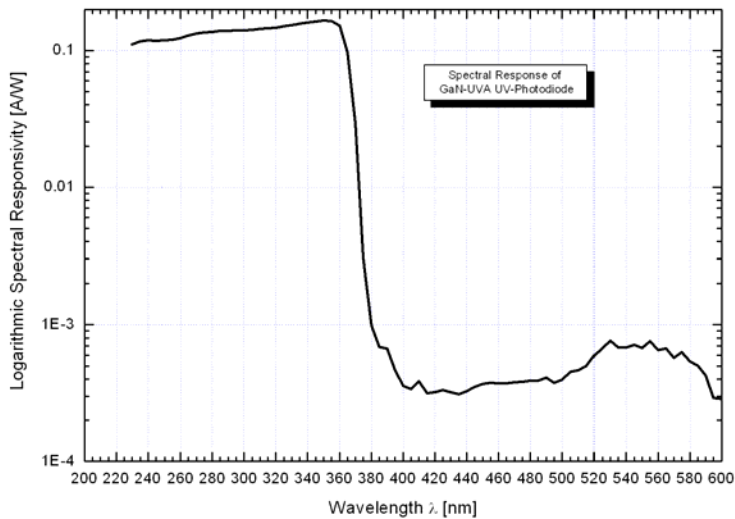


Parameter	Symbol	Value	Unit
Max. spectral sensitivity	S_{\max}	0.14	$A W^{-1}$
Wavelength of max. spectral sensitivity	$\lambda_{S\max}$	350	nm
Range of spectral sensitivity ($S=0.1*S_{\max}$)	-	220 - 370	nm

Linear Spectral Response



Logarithmic Spectral Response

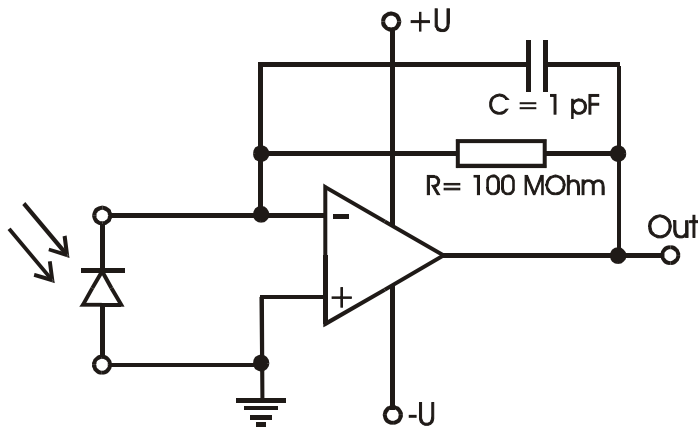


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Application Example



Pin Layout

